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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al.

Title: LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRIC LAYERS

Docket No.: 1303.101US1

Serial No.: 10/602,323

Filed: June 24, 2003

Due Date: July 28, 2006

Examiner: Fernando L Toledo

Group Art Unit: 2823

MS Amendment

Commissioner for Patents

P.O. Box 1450


Alexandria, VA 22313-1450

We are transmitting herewith the following attached items (as indicated with an "X"):


- ☒ Return postcard.
- ☒ Amendment and Response (12 pgs.).
- ☒ Communication Concerning Related Applications (2 pgs.).


If not provided for in a separate paper filed herewith, Please consider this a **PETITION FOR EXTENSION OF TIME** for sufficient number of months to enter these papers and please charge any additional fees or credit overpayment to Deposit Account No. 19-0743.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
Customer Number 21186

By: 
Atty: David R. Cochran
Reg. No. 46,632

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 27 day of July, 2006.


Name


Signature

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
(GENERAL)



Serial 10/602,323

PATENT

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Applicant:	Kie Y. Ahn et al.	Examiner:	Fernando L. Toledo
Serial No.:	10/602,323	Group Art Unit:	2823
Filed:	June 24, 2003	Docket:	1303.101US1
Title:	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRIC LAYERS		

COMMUNICATION CONCERNING RELATED APPLICATIONS

MS Amendment

Commissioner for Patents
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Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related applications in the above-identified patent application:

<u>Serial/Patent No.</u>	<u>Filing Date/Issue Date</u>	<u>Attorney Docket</u>	<u>Title</u>
09780126 6566682	February 9, 2001	1303.008US1	PROGRAMMABLE MEMORY ADDRESS AND DECODE CIRCUITS WITH ULTRA THIN VERTICAL BODY TRANSISTORS
10230951 6720216	August 29, 2002	1303.008US2	PROGRAMMABLE MEMORY ADDRESS AND DECODE CIRCUITS WITH VERTICAL BODY TRANSISTORS
10637727 6903367	August 8, 2003	1303.008US3	PROGRAMMABLE MEMORY ADDRESS AND DECODE CIRCUITS WITH VERTICAL BODY TRANSISTORS
10443021 6970053	May 22, 2003	1303.137US1	ATOMIC LAYER DEPOSITION (ALD) HIGH PERMEABILITY LAYERED MAGNETIC FILMS TO REDUCE NOISE IN HIGH SPEED INTERCONNECTION
11063132	February 22, 2005	1303.137US2	HIGH PERMEABILITY LAYERED MAGNETIC FILMS TO REDUCE NOISE IN HIGH SPEED INTERCONNECTION (As Amended)
11140643	May 27, 2005	1303.141US1	HAFNIUM TITANIUM OXIDE FILMS
11152759	June 14, 2005	1303.144US1	IRIDIUM / ZIRCONIUM OXIDE STRUCTURE
11216958	August 31, 2005	1303.150US1	COBALT TITANIUM OXIDE DIELECTRIC FILMS
11216474	August 31, 2005	1303.152US1	LANTHANUM ALUMINUM OXYNITRIDE DIELECTRIC FILMS
11215578	August 29, 2005	1303.154US1	ZIRCONIUM-DOPED GADOLINIUM OXIDE FILMS

11459792	July 25, 2006	1303.092US2	ZrAlxOy DIELECTRIC LAYERS
11297567	December 8, 2005	1303.157US1	LANTHANIDE YTTRIUM ALUMINUM OXIDE DIELECTRIC FILMS
11297741	December 8, 2005	1303.161US1	HAFNIUM TANTALUM TITANIUM OXIDE FILMS
11329025	January 10, 2006	1303.163US1	GALLIUM LANTHANIDE OXIDE FILMS
11427569	June 29, 2006	1303.079US2	LANTHANIDE DOPED TiOX DIELECTRIC FILMS
11457978	July 17, 2006	1303.061US4	ATOMIC LAYER DEPOSITED NANOLAMINATES OF HfO2/ZrO2 FILMS AS GATE DIELECTRICS
11457987	July 17, 2006	1303.061US5	ATOMIC LAYER DEPOSITED NANOLAMINATES OF Hf O2/ZrO2 FILMS AS GATE DIELECTRICS
11460203	July 26, 2006	1303.133US2	ATOMIC LAYER DEPOSITION OF Zr3N4/ZrO2 FILMS AS GATE DIELECTRICS
11216542	August 30, 2005	303.903US1	GRADED DIELECTRIC LAYERS
11197184	August 4, 2005	303.904US1	CONDUCTIVE NANOPARTICLES


Continuations and divisionals may be later filed on the cases listed above, or cited to the Examiner in any previous Communication Concerning Related Applications. Applicants request that the Examiner review all continuations and divisionals of the above-listed or previously-cited patent applications before allowing the claims of the present patent application.

Respectfully submitted,
KIE Y. AHN ET AL.

By Applicants' Representatives,
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Date 27 July 2006

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